SCAS289G - JANUARY 1993 - REVISED SEPTEMBER 1998

- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC} = 3.3 V, T_A = 25°C
- Inputs Accept Voltages to 5.5 V
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

D. DB. DGV. OR PW PACKAGE (TOP VIEW) 16 NCC 1CLK 1K **□** 2 15 1 1 CLR 1J 14 1 2 CLR 3 1PRE [4 13 2CLK 1Q **∏** 5 12**∏** 2K 1Q 11 **∏** 2J 2Q 10 2PRE GND 8 9 2Q

description

This dual negative-edge-triggered J-K flip-flop is designed for 1.65-V to 3.6-V V_{CC} operation.

A low level at the preset (PRE) or clear (CLR) inputs sets or resets the outputs, regardless of the levels of the other inputs. When PRE and CLR are inactive (high), data at the J and K inputs meeting the setup time requirements is transferred to the outputs on the negative-going edge of the clock pulse. Clock triggering occurs at a voltage level and is not directly related to the rise time of the clock pulse. Following the hold-time interval, data at the J and K inputs can be changed without affecting the levels at the outputs. The SN74LVC112A can perform as a toggle flip-flop by tying J and K high.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

The SN74LVC112A is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

		INPUTS			OUTI	PUTS
PRE	CLR	CLK	J	K	Q	Q
L	Н	Х	Χ	Х	Н	L
Н	L	Χ	Χ	Χ	L	Н
L	L	X	Χ	X	н†	H [†]
Н	Н	\downarrow	L	L	Q ₀	\overline{Q}_0
Н	Н	\downarrow	Н	L	Н	L
Н	Н	\downarrow	L	Н	L	Н
Н	Н	\downarrow	Н	Н	Toggle	
Н	Н	Н	Χ	X	Q_0	\overline{Q}_0

The output levels in this configuration may not meet the minimum levels for V_{OH}. Furthermore, this configuration is unstable; that is, it does not persist when either PRE or CLR returns to its inactive (high) level.



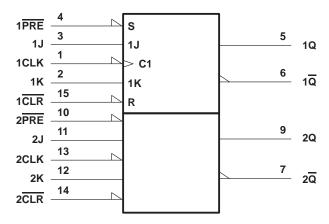
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC is a trademark of Texas Instruments Incorporated.



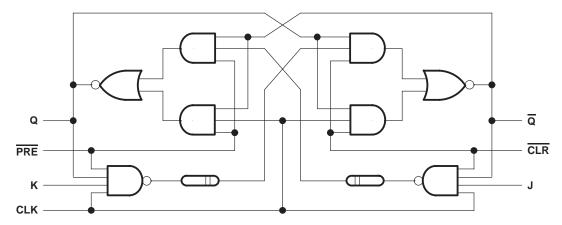
SCAS289G - JANUARY 1993 - REVISED SEPTEMBER 1998

logic symbol†



[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each flip-flop (positive logic)





SCAS289G – JANUARY 1993 – REVISED SEPTEMBER 1998

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}		0.5 V to 6.5 V
Input voltage range, V _I (see Note 1)		
Output voltage range, V _O (see Notes 1 and 2)	($0.5 \text{ V to V}_{CC} + 0.5 \text{ V}$
Input clamp current, I_{IK} ($V_I < 0$)		–50 mA
Output clamp current, I _{OK} (V _O < 0)		–50 mA
Continuous output current, IO		±50 mA
Continuous current through V _{CC} or GND		±100 mA
Package thermal impedance, θ_{JA} (see Note 3):	D package	113°C/W
-	DB package	131°C/W
	DGV package	180°C/W
	PW package	149°C/W
Storage temperature range, T _{stg}		–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. The value of V_{CC} is provided in the recommended operating conditions table.
- 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
\/	Cumply yeltogo	Operating	1.65	3.6	V	
Vcc	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
VIН	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	Data retention only VCC = 1.65 V to 1.95 V VCC = 2.3 V to 2.7 V 1.7 VCC = 2.7 V to 3.6 V 2 VCC = 1.65 V to 1.95 V 0.35 × V VCC = 2.3 V to 2.7 V 0.7 VCC = 2.3 V to 3.6 V 0 VCC = 2.7 V to 3.6 V VCC = 2.3 V VCC = 2.3 V VCC = 2.3 V VCC = 2.3 V VCC = 2.7 V VCC = 3 V VCC = 3 V VCC = 2.7 V 12 VCC = 2.7 V 15 VCC = 2.7 V VCC = 2.7 V VCC = 2.7 V VCC = 3 V VCC = 2.7 V VCC = 2.7 V VCC = 3 V VCC = 2.7 V VCC = 3 V VCC = 3 V VCC = 3 V VCC = 3 V			
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}		
VIL	Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	0.8			
٧ _I	Input voltage	•	0	5.5	V	
٧o	Output voltage		0	Vcc	V	
		V _{CC} = 1.65 V		-4		
	High-level output current	V _{CC} = 2.3 V		-8	mA	
IОН	nigri-ievei output current	V _{CC} = 2.7 V		-12		
		V _{CC} = 3 V		-24		
		V _{CC} = 1.65 V		4		
	Lave lavel autout avenue	V _{CC} = 2.3 V		8	A	
lOL	Low-level output current	V _{CC} = 2.7 V		12	mA	
				24		
Δt/Δν	Input transition rise or fall rate	-	0	10	ns/V	
T _A	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



SCAS289G - JANUARY 1993 - REVISED SEPTEMBER 1998

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP†	MAX	UNIT
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2			
	I _{OH} = -4 mA	1.65 V	1.2			
\/a	I _{OH} = -8 mA	2.3 V	1.7			V
VOH	12 70	2.7 V	2.2			V
	I _{OH} = -12 mA	3 V	2.4			
	I _{OH} = -24 mA	3 V	2.2			
	I _{OL} = 100 μA	1.65 V to 3.6 V			0.2	
	I _{OL} = 4 mA	1.65 V			0.45	
V _{OL}	I _{OL} = 8 mA	2.3 V			0.7	V
	I _{OL} = 12 mA	2.7 V			0.4	
	I _{OL} = 24 mA	3 V			0.55	
lį	V _I = 5.5 V or GND	3.6 V			±5	μΑ
lcc	$V_I = V_{CC}$ or GND, $I_O = 0$	3.6 V			10	μΑ
ΔlCC	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	2.7 V to 3.6 V			500	μА
C _i	V _I = V _{CC} or GND	3.3 V		4.5		pF

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

			V _{CC} =		V _{CC} =		V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX		
f _{clock}	Clock frequency			‡		‡		150		150	MHz	
t _W	Pulse duration, CLK high or low		‡		‡		3.3		3.3		ns	
	Octor Coc	Data before CLK↓	‡		‡		2.3		3.1			
t _{su}	Setup time	PRE or CLR inactive	‡		‡		1.1		2.4		ns	
t _h	Hold time, data after CLK↓		‡		‡		0.7		2.5		ns	

[‡]This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} =		VCC =	2.5 V 2 V	V _{CC} =	2.7 V	V _{CC} =	3.3 V ±	0.3 V	UNIT	
	(INFOT)	(001F01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MIN TYP MAX			
	f _{max}			‡		‡		150		150			MHz
^t pd	CLR or PRE	0	‡	‡	‡	‡		5.5	1	3.4	4.8	no	
	CLK	Q or Q	‡	‡	‡	‡		7.1	1	3.5	5.9	ns	

[‡] This information was not available at the time of publication.

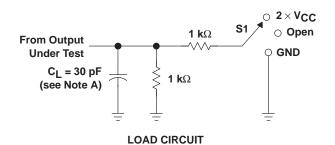


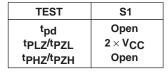
operating characteristics, T_A = 25°C

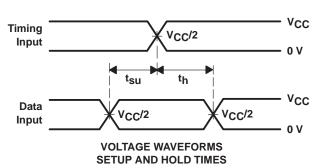
PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V	UNIT
			TYP	TYP	TYP	
C _{pd}	Power dissipation capacitance per flip-flop	f = 10 MHz	†	†	24	pF

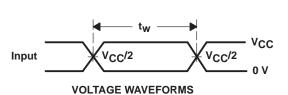
[†] This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 V \pm 0.15 V$

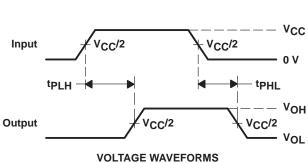




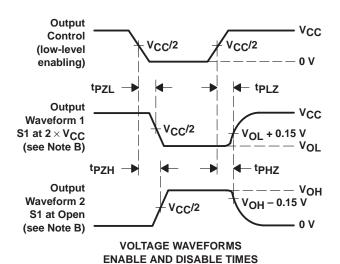




PULSE DURATION



PROPAGATION DELAY TIMES



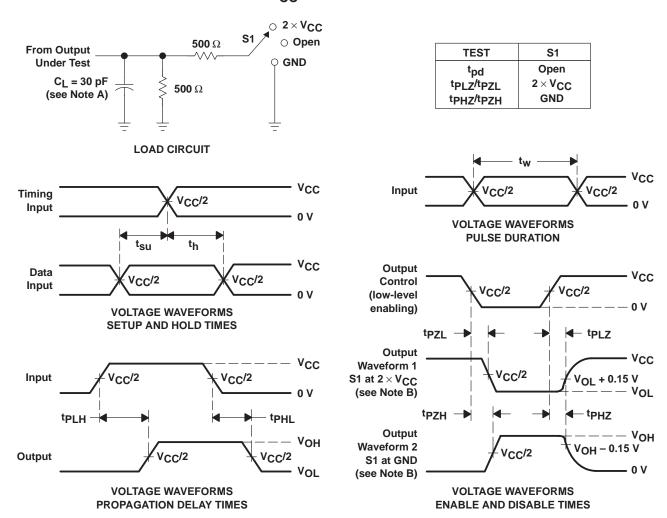
NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$



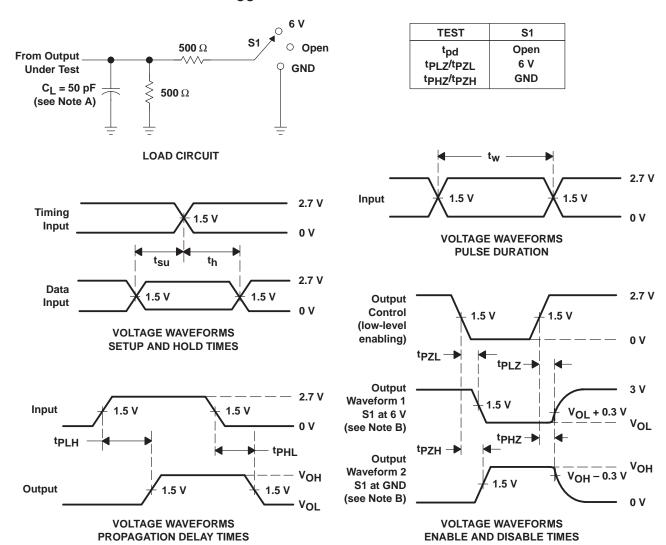
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50~\Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzl and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.7 \text{ V}$ AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated